

Silicon NPN Power Transistors

2SC3895

DESCRIPTION

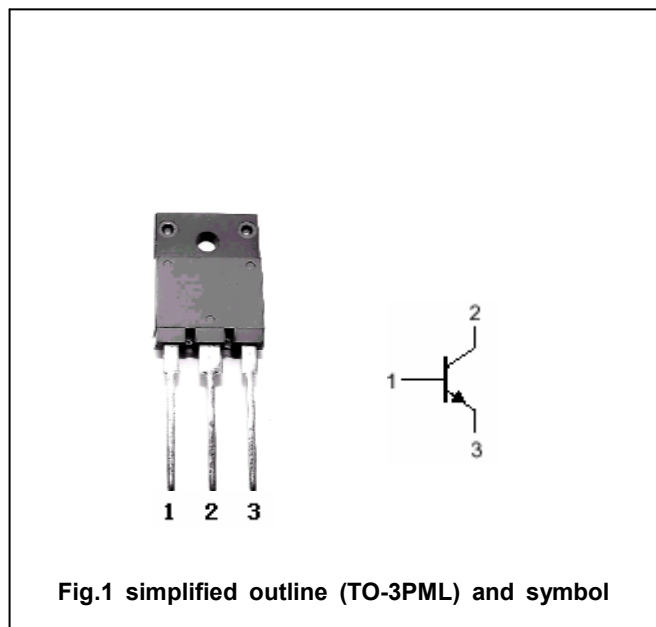
- With TO-3PML package
- High speed
- High breakdown voltage
- High reliability

APPLICATIONS

- Ultrahigh-definition CRT display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		16	A
P_C	Collector dissipation	$T_a=25^\circ\text{C}$	3.0	W
		$T_C=25^\circ\text{C}$	60	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.1A ; I_B=0$	800			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=1.2A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A ; I_B=1.2A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800V ; I_E=0$			10	μA
I_{CES}	Collector cut-off current	$V_{CE}=1500V ; R_{BE}=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=4V ; I_C=0$			1.0	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=5V$	8			
h_{FE-2}	DC current gain	$I_C=5A ; V_{CE}=5V$	4		8	

Switching times

t_{stg}	Storage time	$I_C=4A ; V_{CC}=200V$ $I_{B1}=0.8A ; I_{B2}=1.6A$ $R_L=50\Omega$			3.0	μs
t_f	Fall time			0.1	0.2	μs

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PACKAGE OUTLINE

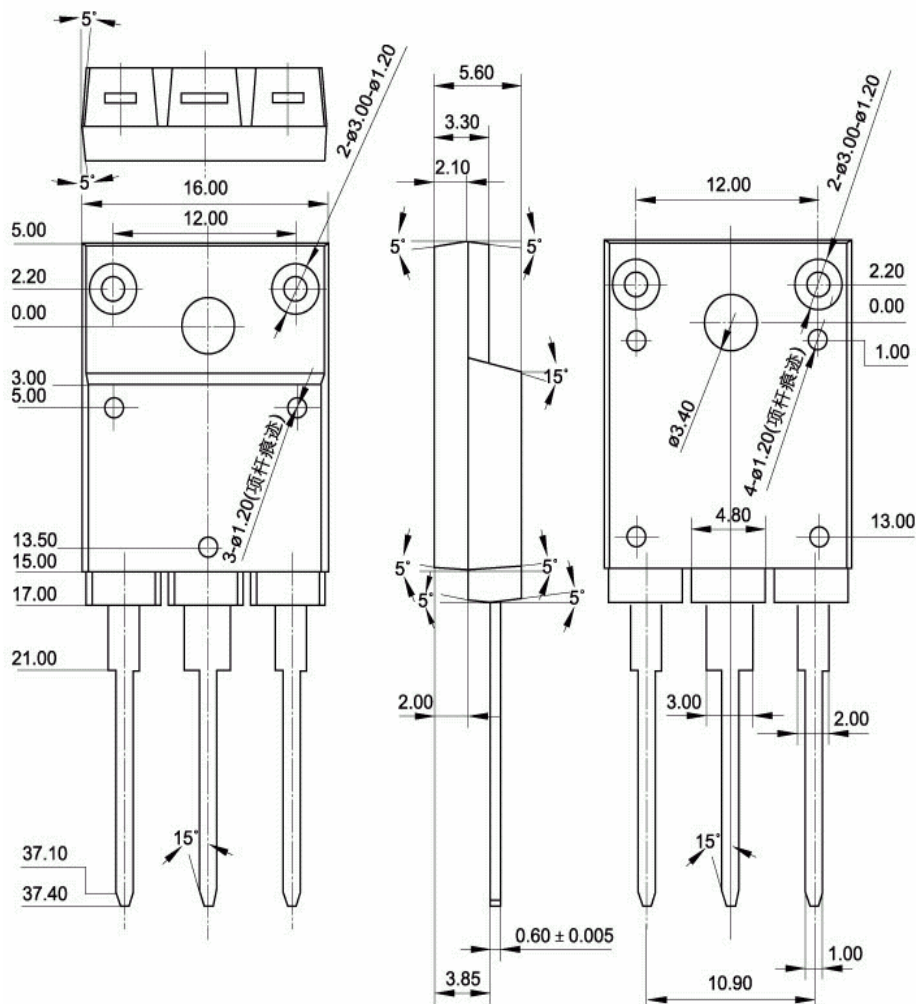


Fig.2 outline dimensions

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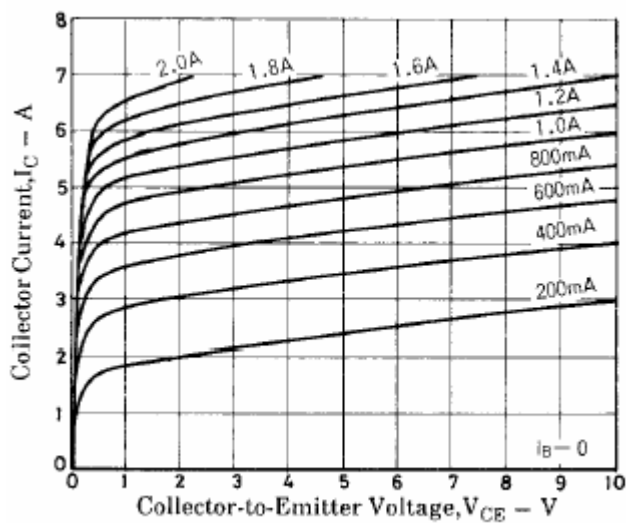


Fig.3 Static Characteristic

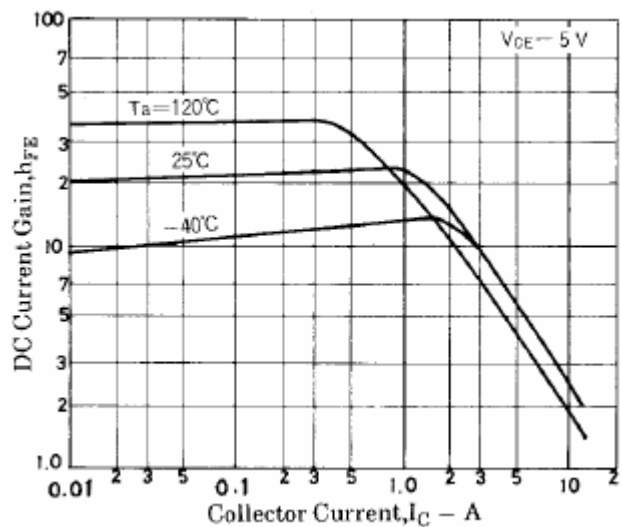


Fig.4 DC current Gain

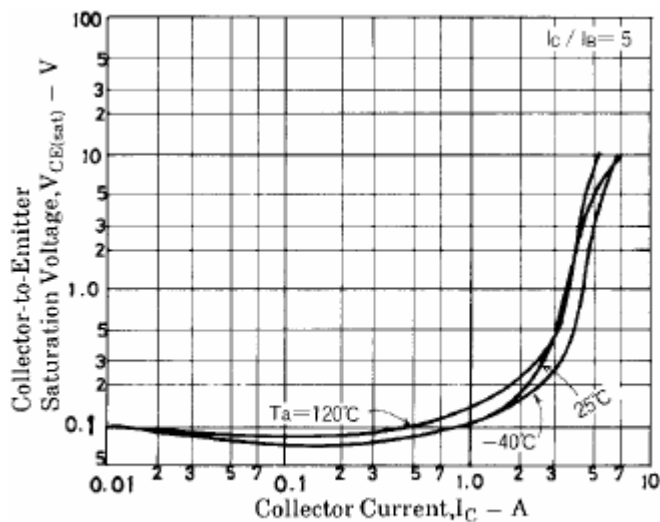


Fig.5 Collector-Emmitter Saturation Voltage

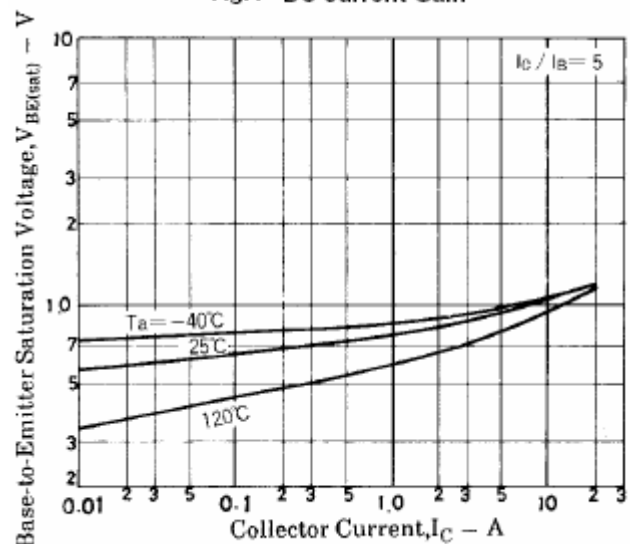


Fig.6 Base-Emmitter Saturation Voltage

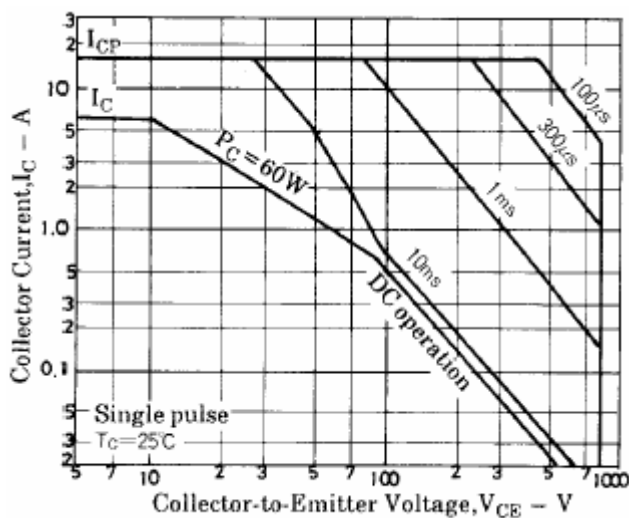


Fig.7 Safe Operating Area